

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	2	("0221315").PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/08/11 09:15
L2	1	method adj electroplating adj copper with formed adj diluting	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/11 09:15
S1	1135	electrolytic adj clean\$3	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/11 09:14
S2	52064	("205").CLAS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/07/25 12:57
S3	282	S1 and S2	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/25 12:58
S4	5	electropolish with clean	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/25 13:08
S5	2	("20020074242").PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/07/25 13:00
S6	8	electropolish with cleaning	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/25 13:09

S7	0	taiwan adj semiconductor adj manufacturing.ti.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/01 16:44
S8	1	electropolish with seed adj layer	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/01 16:45
S9	815	polish\$5 with seed adj layer	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/01 16:45
S10	35	electropolish\$5 with seed adj layer	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/01 17:01
S11	815	polish\$5 with seed adj layer	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/01 16:57
S12	114	polish\$5 near5 seed adj layer	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/01 16:58
S13	12	electrolytic adj polish\$5 with seed adj layer	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/01 17:13
S14	2	("20020068438").PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/08/01 17:24

S15	502	planariz\$5 with seed adj layer	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/01 17:25
S16	72	planariz\$5 near5 seed adj layer	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/01 17:25
S17	0	electrolytic adj clean\$3 same seed adj layer	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/01 17:48
S18	49	electrolytic adj clean\$3 same substrate	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/01 17:33
S19	56	electrolytic adj clean\$3 adj method	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/01 17:33
S20	17	electrolytic adj clean\$3 with (via vias trench trenches)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/01 17:45
S21	4	electrolytic adj clean\$3 with remov\$5 with particle	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/01 17:45
S22	1047	clean\$3 same seed adj layer	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/01 17:48

S23	470	clean\$3 with seed adj layer	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/01 17:48
S24	530	clean\$3 with via adj opening	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/01 17:48
S25	238	clean\$3 near8 via adj opening	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/01 17:52
S26	231	clean\$3 near8 seed adj layer	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/01 17:52
S27	0	qingtang	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/09 18:02
S28	20256	jiang	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/09 18:02
S29	23	tobby	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/09 18:02
S30	745	semiconductor.as. and internat\$6. as.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/09 18:06

S31	1369783	clean\$3	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/09 18:03
S32	197	S30 and S31	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/09 18:03
S33	548842	clean\$3.ab.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/09 18:03
S34	20	S30 and S33	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/09 18:03
S35	79750	("204").CLAS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/08/09 18:06
S36	52118	("205").CLAS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/08/09 18:05
S37	15556	S35 and S36	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/09 18:06
S38	2138	semiconductor.as. and (internat\$6. as. int.as.)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/09 18:06

S39	3	S37 and S38	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/09 18:06
S40	2	("20030201185").PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/08/10 14:34
S41	2	("6309528").PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/08/10 14:34
S42	2	("6652727").PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/08/10 14:34
S43	2	("6793796").PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/08/10 14:49
S44	214157	(polyethylene polypropylene) adj glycol	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/10 15:20
S45	336016	surfactant	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/10 14:53
S46	19440	S44 with S45	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/10 14:53

S47	24062	non adj ionic adj surfactant	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/10 14:53
S48	8677	S44 and S47	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/10 14:56
S49	79750	("204").CLAS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/08/10 14:54
S50	52118	("205").CLAS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/08/10 14:54
S51	15556	S49 and S50	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/10 16:47
S52	3	S44 and S47 and S51	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/10 14:54
S53	2382	S44 with S47	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/10 14:57
S54	1	S53 and S51	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/10 14:56

S55	118	(polyethylene polypropylene) adj glycol with electroplating	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/10 15:23
S56	36460	(polyethylene polypropylene) adj glycol with molecular adj weight	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/10 15:23
S57	343	(polyethylene polypropylene) adj glycol with molecular adj weight and electroplating	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/10 16:14
S58	1954	(polyethylene polypropylene) adj glycol with alkanol	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/10 16:15
S59	18	(polyethylene polypropylene) adj glycol with alkanol and electroplating	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/10 16:44
S60	9815	copper adj sulfate and sulfuric adj acid	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/10 16:44
S61	2130	copper adj sulfate and sulfuric adj acid and electroplating	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/10 16:44
S62	226	copper adj sulfate and sulfuric adj acid and electroplating and S51	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/10 16:46



S63	1430	copper adj sulfate and sulfuric adj acid and (polyethylene polypropylene) adj glycol	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/10 16:47
S64	39	copper adj sulfate and sulfuric adj acid and (polyethylene polypropylene) adj glycol and S51	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/10 16:47
S65	116312	S49 S50	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/10 16:47
S66	266	copper adj sulfate and sulfuric adj acid and (polyethylene polypropylene) adj glycol and S65	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/10 16:48
S67	71	copper adj sulfate and sulfuric adj acid and (polyethylene polypropylene) adj glycol with molecular adj weight and S65	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/10 16:48